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Abstract of the Disclosure

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Apparatus for Atomic Layer Deposition

5 A trap 315 with a residence time at least equal to one complete cycle time of an
atomic layer deposition (ALD) process traps the gaseous effluent from a reaction
chamber 211 and reaction products before the effluent can enter a backing pump 317.
The trap 315 may be connected directly to the reaction chamber 211 or indirectly
through a process pump 313. The trap 315 is advantageously used in atomic layer
10 deposition processes.

Fig. 3